

# TEA1611T

## Zero voltage switching resonant converter controller

Rev. 01 — 7 September 2009

Product data sheet

### 1. General description

The TEA1611T is a monolithic integrated circuit implemented in a high voltage Diffusion Metal Oxide Semiconductor (DMOS) process, which is a high voltage controller for a zero voltage switching resonant converter. The IC provides the drive function for two discrete power MOSFETs in a half-bridge configuration. It also includes a level-shift circuit, an oscillator with accurately programmable frequency range, a latched shut-down function and a transconductance error amplifier.

To guarantee an accurate 50 % switching duty factor, the oscillator signal passes through a divide-by-two flip-flop before being fed to the output drivers.

The circuit is very flexible and enables a broad range of applications for different mains voltages.

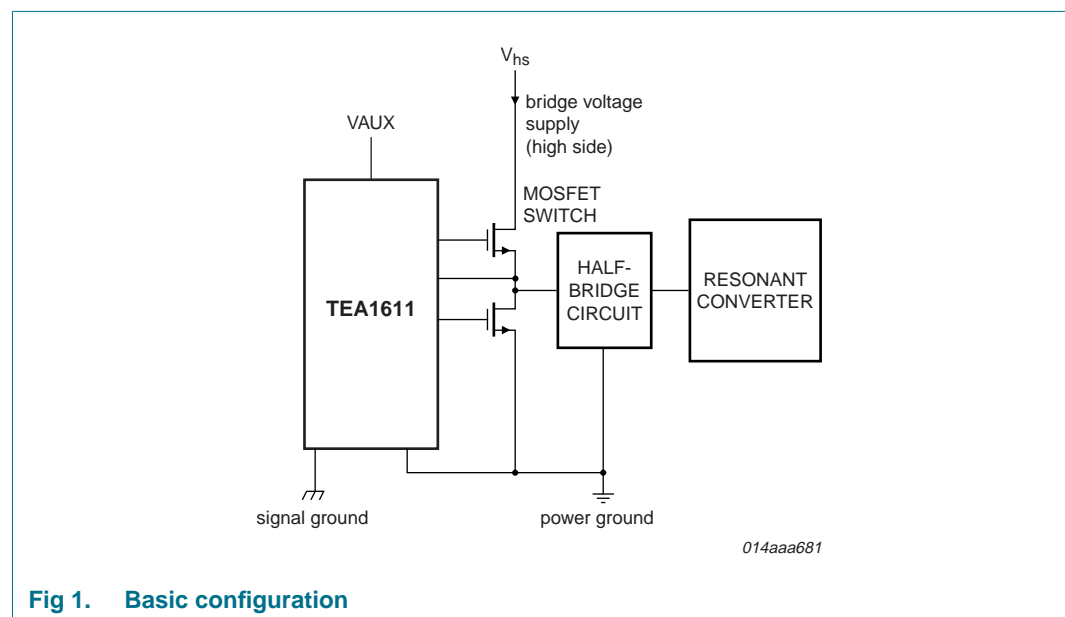


Fig 1. Basic configuration

### 2. Features

- Integrated high voltage level-shift function
- Integrated high voltage bootstrap diode
- Low start-up current (green function)
- Adjustable non-overlap time
- Internal OverTemperature Protection (OTP)
- OverCurrent Protection (OCP) that activates a shut-down timer

- Soft start timing pin
- Transconductance error amplifier for ultra high-ohmic regulation feedback
- Latched shut-down circuit for OverVoltage Protection (OVP)
- Adjustable minimum and maximum frequencies
- UnderVoltage LockOut (UVLO)
- Fault latch reset input
- Wide (max 20 V) supply voltage range

### 3. Applications

- TV and monitor power supplies
- High voltage power supplies

### 4. Ordering information

Table 1. Ordering information

Type number	Package		
	Name	Description	Version
TEA1611T	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1

5. Block diagram

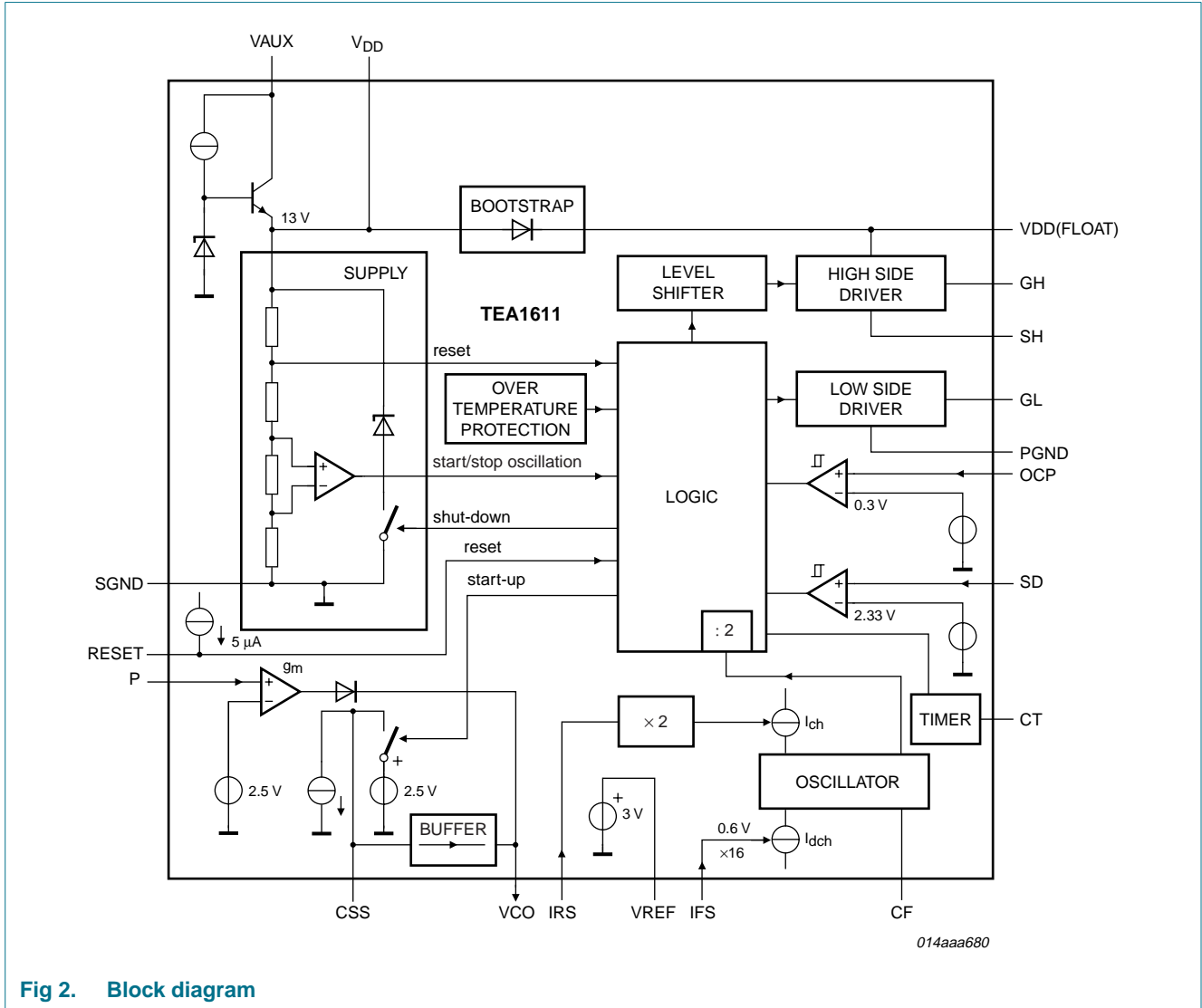
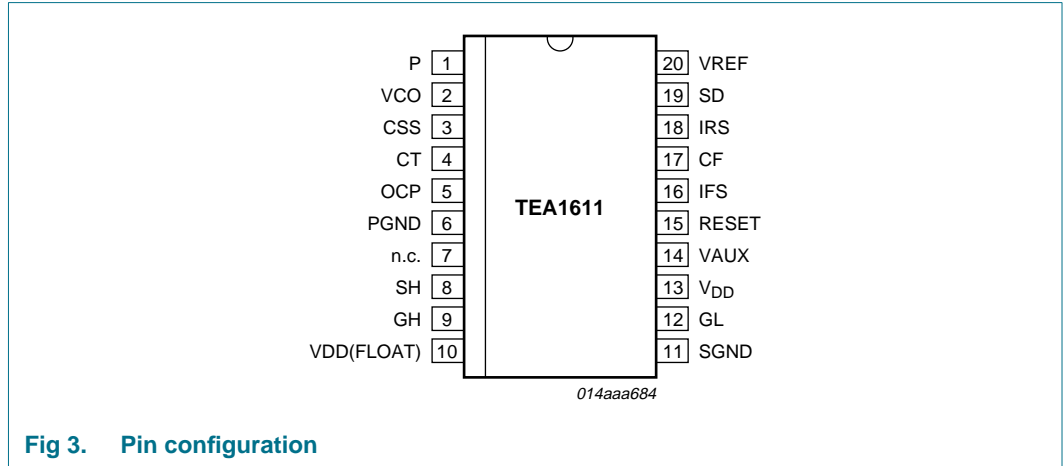


Fig 2. Block diagram

## 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
P	1	error amplifier non-inverting input
VCO	2	error amplifier output
CSS	3	soft start capacitor input
CT	4	timer capacitor input
OCP	5	overcurrent protection input
PGND	6	power ground
n.c.	7	not connected <sup>[1]</sup>
SH	8	high side switch source connection
GH	9	high side switch gate connection
VDD(FLOAT)	10	floating supply high side driver
SGND	11	signal ground
GL	12	low side switch gate connection
V <sub>DD</sub>	13	supply voltage
VAUX	14	auxiliary supply voltage
RESET	15	latch reset input
IFS	16	oscillator discharge current input
CF	17	oscillator capacitor
IRS	18	oscillator charge input current
SD	19	shut-down input
VREF	20	reference voltage

[1] Provided as a high voltage spacer

## 7. Functional description

### 7.1 Start-up

When the applied voltage at  $V_{DD}$  reaches  $V_{DD(Init)}$  (see [Figure 4](#)), the low side power switch is turned on while the high side power switch remains in the non-conducting state. This start-up output state guarantees the initial charging of the bootstrap capacitor ( $C_{boot}$ ) used for the floating supply of the high side driver.

During start-up, the voltage on the frequency capacitor pin (CF) is zero and defines the start-up state. The voltage at the soft start pin (CSS) is set to 2.5 V. The CSS pin voltage is copied to the VCO pin via a buffer and switching starts at about 80 % of the maximum frequency at the moment  $V_{DD}$  reaches the start level.

The start-up state is maintained until  $V_{DD}$  reaches the start level (13.5 V), the oscillator is activated and the converter starts operating.

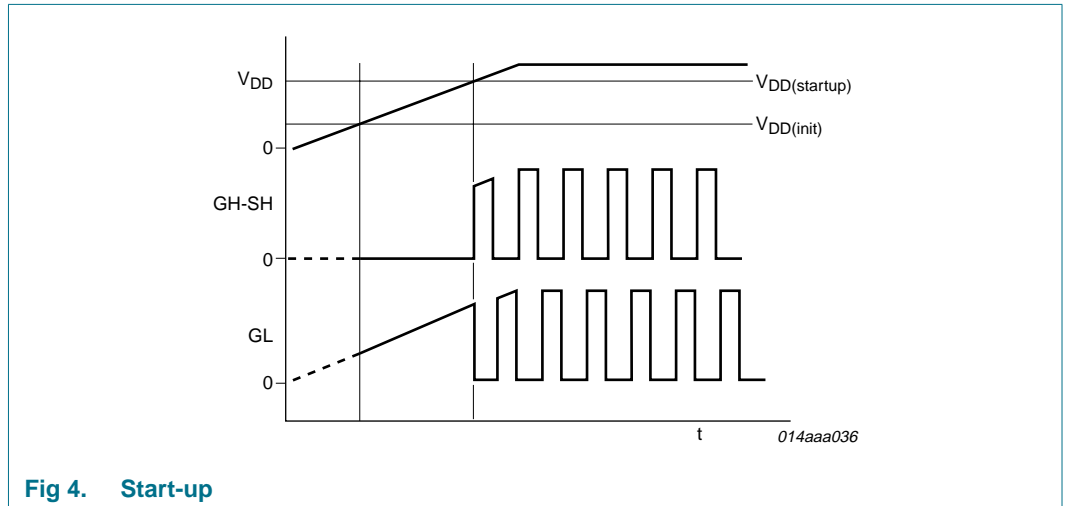


Fig 4. Start-up

### 7.2 Oscillator

The internal oscillator is a current-controlled sawtooth oscillator. The frequency of the sawtooth is determined by the external capacitor  $C_f$  and the currents flowing into the IFS and IRS pins.

The minimum frequency and the non-overlap time are set by the capacitor  $C_f$  and the resistors  $R_{f(min)}$  and  $R_{no}$ . The maximum frequency is set by resistor  $R_{\Delta f}$  (see [Figure 7](#)). The oscillator frequency is exactly twice the bridge frequency to achieve an accurate 50 % duty factor. An overview of the oscillator and driver signals is given in [Figure 5](#).

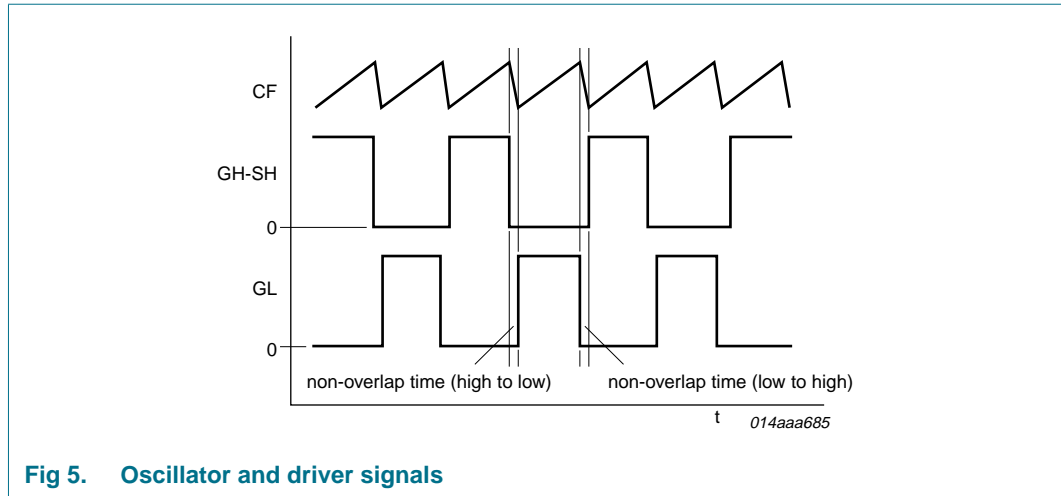


Fig 5. Oscillator and driver signals

### 7.3 Non-overlap time resistor

The non-overlap time resistor  $R_{no}$  is connected between the 3 V reference pin (VREF) and the IFS current input pin (see Figure 7). The voltage on the IFS pin is kept at a temperature-independent value of 0.6 V. The current that flows into the IFS pin is determined by the value of resistor's  $R_{no}$  2.4 V voltage drop divided by its value. The IFS input current equals 1/16 of the discharge current of capacitor  $C_f$  and determines the falling slope of the oscillator.

The falling slope time is used to create a non-overlap time ( $t_{no}$ ) between two successive switching actions of the half-bridge switches:

$$I_{IFS} = \frac{2.4V}{R_{no}}$$

$$t_{no} = \frac{C_f \times \Delta V_{Cf}}{16 \times I_{IFS}}$$

### 7.4 Minimum frequency resistor

The  $R_{f(min)}$  resistor is connected between the VREF pin (3 V reference voltage) and the IRS current input (kept at a temperature-independent voltage level of 0.6 V). The charge current of the capacitor  $C_f$  is twice the current flowing into the IRS pin.

The  $R_{f(min)}$  resistor has a voltage drop of 2.4 V and its resistance defines the minimum charge current (rising slope) of the  $C_f$  capacitor if the control current is zero. The minimum frequency is defined by this minimum charge current ( $I_{IRS1}$ ) and the discharge current:

$$I_{IRS1} = \frac{2.4V}{R_{f(min)}}$$

$$t_{IRS1} = \frac{C_f \times \Delta V_{Cf}}{2 \times I_{IRS1}}$$

$$f_{osc(min)} = \frac{1}{t_{no} \times t_{IRS1}}$$

$$f_{bridge(min)} = \frac{f_{osc(min)}}{2}$$

## 7.5 Maximum frequency resistor

The output voltage is regulated by changing the frequency of the half-bridge converter. The maximum frequency is determined by the  $R_{\Delta f}$  resistor which is connected between the error amplifier output VCO and the oscillator current input pin IRS. The current that flows through the  $R_{\Delta f}$  resistor ( $I_{IRS2}$ ) is added to the current flowing through the  $R_{f(min)}$  resistor. As a result, the charge current ICF increases and the oscillation frequency increases. As the falling slope of the oscillator is constant, the relationship between the output frequency and the charge current is not a linear function (see [Figure 6](#) and [Figure 7](#)):

$$I_{IRS2} = \frac{V_{VCO} - 0.6}{R_{\Delta f}}$$

$$t_{IRS2} = \frac{C_f \times \Delta V_{Cf}}{2 \times (I_{IRS1} + I_{IRS2})}$$

The maximum output voltage of the error amplifier and the value of  $R_{\Delta f}$  determine the maximum frequency:

$$I_{IRS2(max)} = \frac{V_{VCO(max)} - 0.6}{R_{\Delta f}}$$

$$t_{IRS(min)} = \frac{C_f \times \Delta V_{Cf}}{2 \times (I_{IRS2} + I_{IRS2(max)})}$$

$$f_{osc(max)} = \frac{1}{T_{OSC}}$$

$$f_{bridge(max)} = \frac{f_{osc(max)}}{2}$$

$$T_{OSC} = t_{IRS(min)} + t_{no}$$

The frequency of the oscillator depends on the value of capacitor  $C_f$ , the peak-to-peak voltage swing  $V_{CF}$  and the charge and discharge currents. The accuracy of the oscillator frequency decreases at higher frequencies due to delays in the circuit.

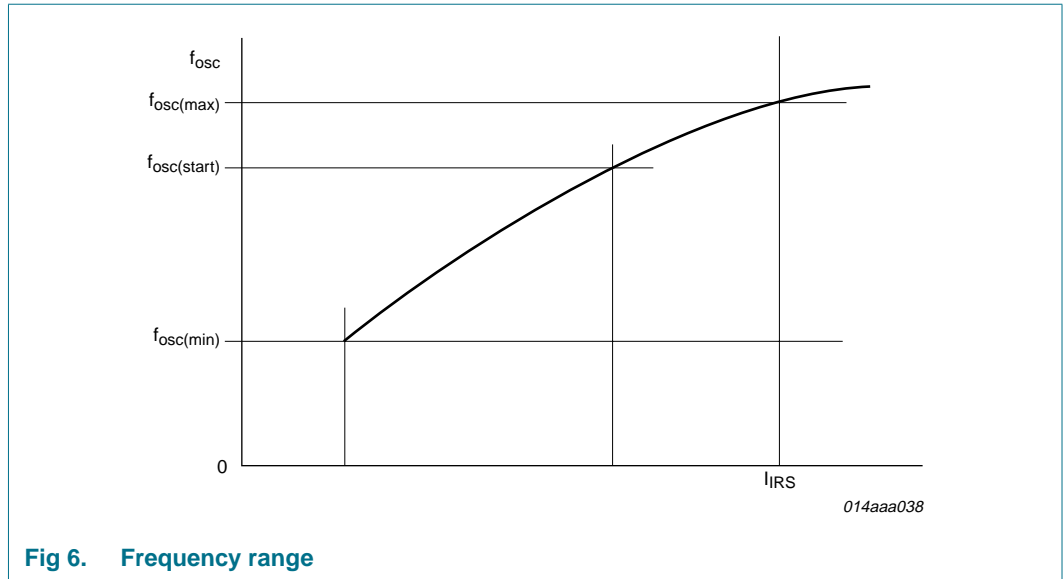


Fig 6. Frequency range

## 7.6 Error amplifier

The error amplifier is a transconductance amplifier. The output current at pin VCO is determined by the amplifier transconductance, the differential voltage between input pin P, and the internal 2.5 V reference voltage. The output current  $I_{VCO}$  is fed to the IRS input of the current-controlled oscillator.

The source capability of the error amplifier increases current in the IRS pin with a positive differential input voltage. Therefore the minimum current is determined by resistor  $R_{f(min)}$  and the minimum frequency setting is independent of the characteristics of the error amplifier.

The error amplifier has a maximum output current of 0.5 mA for an output voltage of up to 2.5 V. If the source current decreases, the oscillator frequency also decreases resulting in a higher regulated output voltage.

During start-up, the output voltage of the amplifier is connected to the soft start (CSS) pin via a buffer. This will hold the VCO pin at a constant value of 2.5 V.

## 7.7 Soft start

The CSS pin voltage is copied to the VCO pin via a buffer. This buffer only has a source capability, i.e. it can only charge the VCO pin. This means that the error amplifier output can increase the VCO pin voltage above the CSS voltage level.

At start-up the soft start capacitor is charged to 2.5 V setting a start-up frequency of about 80 % of the maximum frequency. After start-up the external soft start capacitor is discharged by  $I_{start(soft)}$ . The VCO pin voltage will follow the CSS voltage (discharging takes place via  $R_{\Delta f}$ ) and the frequency sweeps down. The CSS capacitor will determine the frequency sweep rate. When the circuit comes into regulation, the error amplifier output will control the VCO pin voltage and the CSS voltage will sweep down further to zero volt.



**7.8 Overcurrent protection and timer**

The OCP input continuously compares the OCP pin voltage with VREF. When the OCP pin voltage is higher than VREF, the timer capacitor CT will be charged with I<sub>ch</sub> during the next full CF cycle. Else the timer capacitor will be discharged with I<sub>leak</sub>.

In case the CT voltage exceeds V<sub>trip(H)</sub>, the TEA1611T will switch over to shut-down mode. The timer capacitor will be discharged with I<sub>dch</sub> until the CT voltage reaches V<sub>trip(L)</sub> after which a soft start cycle is started.

**7.9 Shut-down**

The shut-down input (SD) has an accurate threshold level of 2.33 V. When the voltage on input SD reaches 2.33 V, the TEA1611T enters shut-down mode.

During shut-down mode, pin V<sub>DD</sub> is clamped by an internal 12 V Zener diode with a 1 mA input current. This clamp prevents V<sub>DD</sub> rising above the rating of 14 V due to low supply current to the TEA1611T in shut-down mode.

When the TEA1611T is in the shut-down mode, it can be activated again only by lowering V<sub>DD</sub> below the V<sub>DD(rst)</sub> level (typically 5.3 V) or by making the reset input active. The shut-down latch is then reset and a new start-up cycle can begin.

In shut-down mode the GL pin is HIGH and the GH pin is LOW. In this way the bootstrap capacitor remains charged, allowing a new, well defined cycle to start after a reset.

**7.10 OverTemperature Protection (OTP)**

The TEA1611T continuously monitors its temperature. When the temperature exceeds the T<sub>otp(act)</sub> level, the TEA1611T will switch to shut-down mode.

**7.11 Latch reset input**

The internal shut-down latch can be reset via the reset input. This input is active LOW.

**7.12 VAUX input**

When the IC is oscillating the start-up resistor is not able to deliver the supply current so that an auxiliary supply (for instance via an auxiliary winding or a dV/dt supply) is needed. The VAUX input facilitates a series regulator which regulates its output voltage (= V<sub>DD</sub> voltage) to V<sub>DD(reg)</sub>.

**8. Limiting values**

**Table 3. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit
<b>Supply voltages</b>					
V <sub>drv(hs)</sub>	high-side driver voltage		0	600	V
V <sub>DD</sub>	supply voltage	[1]	0	14	V
V <sub>CC(AUX)</sub>	auxiliary supply voltage	[1]	0	20	V

**Table 3. Limiting values ...continued**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
<b>Voltage on pins P, SD, RESET and OCP</b>						
$V_I$	input voltage		0	5	V	
<b>Currents</b>						
$I_{IFS}$	current on pin IFS		-	1/16	mA	
$I_{IRS}$	current on pin IRS		-	1	mA	
$I_{VREF}$	current on pin VREF		-	-2	mA	
<b>Power and temperature</b>						
$P_{tot}$	total power dissipation	$T_{amb} < 70\text{ °C}$	-	0.8	W	
$T_{amb}$	ambient temperature	operating	-25	+70	°C	
$T_{stg}$	storage temperature		-25	+150	°C	
<b>Handling</b>						
$V_{ESD}$	electrostatic discharge voltage	Human body model	[2]	-	2000	V
		Machine model	[3]	-	200	V

- [1] It is recommended that a buffer capacitor is placed as close as possible to the VDD pin (as indicated in [Figure 7](#) and in the application note).
- [2] Human body model class 2: equivalent to discharging a 100 pF capacitor through a 1.5 kΩ series resistor.
- [3] Machine model class 2: equivalent to discharging a 200 pF capacitor through a 0.75 mH coil and 10 Ω resistor.

## 9. Thermal characteristics

**Table 4. Thermal characteristics**

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	100	K/W

## 10. Characteristics

**Table 5. Characteristics**

All voltages are referred to the ground pins which must be connected externally; positive currents flow into the IC;  $V_{DD} = 13\text{ V}$  and  $T_{amb} = 25\text{ °C}$ ; tested using the circuit shown in [Figure 7](#), unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>High voltage pins VDD(FLOAT), GH and SH</b>						
$I_{leak}$	leakage current	$V_{DD(F)}$ , $V_{GH}$ and $V_{SH} = 600\text{ V}$	-	-	30	μA
<b>Supply pins <math>V_{DD}</math>, VAUX</b>						
$V_{DD(Init)}$	initial supply voltage	defined driver output; low side on; high side off	-	4	5	V
$V_{DD(startup)}$	start-up supply voltage		12.9	13.4	13.9	V
$V_{DD(stop)}$	stop supply voltage		9.0	9.4	9.8	V
$V_{DD(hys)}$	hysteresis of supply voltage		3.8	4.0	4.2	V

**Table 5. Characteristics ...continued**

All voltages are referred to the ground pins which must be connected externally; positive currents flow into the IC;  $V_{DD} = 13\text{ V}$  and  $T_{amb} = 25\text{ °C}$ ; tested using the circuit shown in [Figure 7](#), unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DD(\text{reg})}$	regulation supply voltage	$VAUX = 17\text{ V}$	-	12.6	-	V
$V_{DD}$	supply voltage	current capability series regulator; $V_{CC(\text{AUX})} = 17\text{ V}$ ; $I_{DD} = 50\text{ mA}$	-	12	-	V
		clamp voltage in shut-down state; low side on; high side off; $I_{DD} = 1\text{ mA}$	11.0	12.0	13.0	V
$V_{rst}$	reset voltage		4.5	5.3	6.0	V
$I_{DD}$	supply current		[1]			
		start-up	210	260	310	$\mu\text{A}$
		operating	-	2.4	-	mA
		shut-down	-	220	270	$\mu\text{A}$

**Reference voltage on pin VREF**

$V_{ref}$	reference voltage	$I_{ref} = 0\text{ mA}$	2.9	3.0	3.1	V
$I_{ref}$	reference current	source only	-2.0	-	-	mA
$Z_o$	output impedance	$I_{ref} = -1\text{ mA}$	-	5.0	-	$\Omega$
TC	temperature coefficient	$I_{ref} = 0\text{ mA}$ ; $T_j = 25\text{ °C}$ to $150\text{ °C}$	-	-0.3	-	mV/K

**Current controlled oscillator pins IRS, IFS, CF**

$I_{ch(\text{CF})\text{min}}$	minimum charge current on pin CF	$I_{IRS} = 15\text{ }\mu\text{A}$ ; $V_{CF} = 2\text{ V}$	28	30	32	$\mu\text{A}$
$I_{ch(\text{CF})\text{max}}$	maximum charge current on pin CF	$I_{IRS} = 200\text{ }\mu\text{A}$ ; $V_{CF} = 2\text{ V}$	340	380	420	$\mu\text{A}$
$V_{IRS}$	voltage on pin IRS	$I_{IRS} = 200\text{ }\mu\text{A}$	590	620	650	mV
$I_{dch(\text{CF})\text{min}}$	minimum discharge current on pin CF	$I_{IFS} = 50/16\text{ }\mu\text{A}$ ; $V_{CF} = 2\text{ V}$	47	50	53	$\mu\text{A}$
$I_{dch(\text{CF})\text{max}}$	maximum discharge current on pin CF	$I_{IFS} = 1/16\text{ }\mu\text{A}$ ; $V_{CF} = 2\text{ V}$	0.89	0.94	0.99	mA
$V_{IFS}$	voltage on pin IFS	$I_{IFS} = 1/16\text{ mA}$	570	600	630	mV
$f_{\text{bridge}(\text{min})}$	minimum bridge frequency	$C_f = 100\text{ pF}$ ; $I_{IFS} = 0.5/16\text{ mA}$ ; $I_{IRS} = 50\text{ }\mu\text{A}$ ; $f_{\text{bridge}} = \frac{f_{osc}}{2}$	156	167	178	kHz
$f_{\text{bridge}(\text{max})}$	maximum bridge frequency	$C_f = 100\text{ pF}$ ; $I_{IFS} = 1/16\text{ mA}$ ; $I_{IRS} = 200\text{ }\mu\text{A}$ ; $f_{\text{bridge}} = \frac{f_{osc}}{2}$	[2] 395	440	485	kHz
$V_{\text{trip}(\text{L})}$	LOW-level trip voltage	pin CF; DC level	-	1.27	-	V
$V_{\text{trip}(\text{H})}$	HIGH-level trip voltage	pin CF; DC level	-	2.97	-	V

**Table 5. Characteristics ...continued**

All voltages are referred to the ground pins which must be connected externally; positive currents flow into the IC;  $V_{DD} = 13\text{ V}$  and  $T_{amb} = 25\text{ }^{\circ}\text{C}$ ; tested using the circuit shown in [Figure 7](#), unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CF(p-p)}$	peak-to-peak voltage on pin CF	DC level	1.6	1.7	1.8	V
$t_{no}$	non-overlap time	$C_f = 100\text{ pF}$ ; $I_{IFS} = 0.5/16\text{ mA}$ ; $I_{IRS} = 50\text{ }\mu\text{A}$	0.58	0.63	0.68	$\mu\text{s}$
$I_{dch(osc)}/I_{IFS}$	oscillator discharge current to current on pin IFS ratio	$I_{IFS} = 0.5/16\text{ mA}$ ;	14.4	16	17.6	
<b>Output drivers</b>						
$I_{source(GH)}$	source current on pin GH	high side; $V_{DD(F)} = 11.2\text{ V}$ ; $V_{SH} = 0\text{ V}$ ; $V_{GH} = 0\text{ V}$	-	300	-	mA
$I_{sink(GH)}$	sink current on pin GH	high side; $V_{DD(F)} = 11.2\text{ V}$ ; $V_{SH} = 0\text{ V}$ ; $V_{GH} = 11.2\text{ V}$	-	480	-	mA
$I_{source(GL)}$	source current on pin GL	low side; $V_{GL} = 0\text{ V}$	-	300	-	mA
$I_{sink(GL)}$	sink current on pin GL	low side; $V_{GL} = 13\text{ V}$	-	580	-	mA
$V_{OH}$	HIGH-level output voltage	pin GH; high side; $V_{DD(F)} = 11.2\text{ V}$ ; $V_{SH} = 0\text{ V}$ ; $I_{GH} = 10\text{ mA}$	-	10.9	-	V
		pin GL; low side; $I_{GL} = 10\text{ mA}$	-	12.6	-	V
$V_{OL}$	LOW-level output voltage	pin GL; high side; $V_{DD(F)} = 11.2\text{ V}$ ; $V_{SH} = 0\text{ V}$ ; $I_{GH} = 10\text{ mA}$	-	0.17	-	V
		pin GL; low side; $I_{GL} = 10\text{ mA}$	-	0.18	-	V
$V_{Fd(bs)}$	bootstrap diode forward voltage	$I_O = 5\text{ mA}$	1.3	1.6	1.9	V
<b>Shut-down input pin SD</b>						
$I_I$	input current	$V_{SD} = 2.33\text{ V}$	-	-	0.5	$\mu\text{A}$
$V_{th(SD)}$	threshold voltage on pin SD		2.26	2.33	2.40	V
<b>Error amplifier pins P, VCO</b>						
$I_{I(cm)}$	common-mode input current	$V_{I(cm)} = 1\text{ V}$	-	-0.1	-0.5	$\mu\text{A}$
$V_{I(cm)}$	common-mode input voltage		-	-	2.5	V
$V_{I(offset)}$	offset input voltage	$V_{I(cm)} = 1\text{ V}$ ; $I_{VCO} = -10\text{ mA}$	-2	0	+2	mV
$g_m$	transconductance	$V_{I(cm)} = 1\text{ V}$ ; source only	-	330	-	$\mu\text{A/mV}$
$G_{ol}$	open-loop gain	$R_L = 10\text{ k}\Omega$ to GND; $V_{I(cm)} = 1\text{ V}$	-	70	-	dB
GB	gain bandwidth product	$R_L = 10\text{ k}\Omega$ to GND; $V_{I(cm)} = 1\text{ V}$	-	5	-	MHz
$V_{VCO(max)}$	maximum VCO voltage	operating; $R_L = 10\text{ k}\Omega$ to GND	3.2	3.6	4.0	V
$I_{VCO(max)}$	maximum VCO current	operating; $V_{VCO} = 1\text{ V}$	-0.4	-0.5	-0.6	mA
$V_O$	output voltage	during start-up; $I_{VCO} = 0.3\text{ mA}$	2.5	2.7	2.9	V

**Table 5. Characteristics ...continued**

All voltages are referred to the ground pins which must be connected externally; positive currents flow into the IC;  $V_{DD} = 13\text{ V}$  and  $T_{amb} = 25\text{ }^{\circ}\text{C}$ ; tested using the circuit shown in [Figure 7](#), unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Reset pin</b>						
$V_{rst}$	reset voltage		2.15	2.4	2.65	V
$V_{rst(hys)}$	hysteresis of reset voltage		-	0.65	-	V
$I_{l(rst)}$	reset input current		-	-	1	$\mu\text{A}$
<b>CSS pin</b>						
$I_{start(soft)}$	soft start current		12	15	18	$\mu\text{A}$
<b>CT pin</b>						
$I_{ch}$	charge current		21	27	33	$\mu\text{A}$
$I_{dch}$	discharge current		8	10	12	$\mu\text{A}$
$I_{leak}$	leakage current		0.1	0.3	1	$\mu\text{A}$
$I_{ch}/I_{dch}$	charge current to discharge current ratio		2.4	2.7	3.0	$\mu\text{A}$
$V_{trip(H)}$	HIGH-level trip voltage		2.7	3	3.3	V
$V_{trip(L)}$	LOW-level trip voltage		0.6	0.7	0.8	V
<b>OCP pin</b>						
$V_{ref}$	reference voltage		280	305	330	mV
<b>OTP</b>						
$T_{otp(act)}$	activation overtemperature protection temperature		120	135	150	$^{\circ}\text{C}$

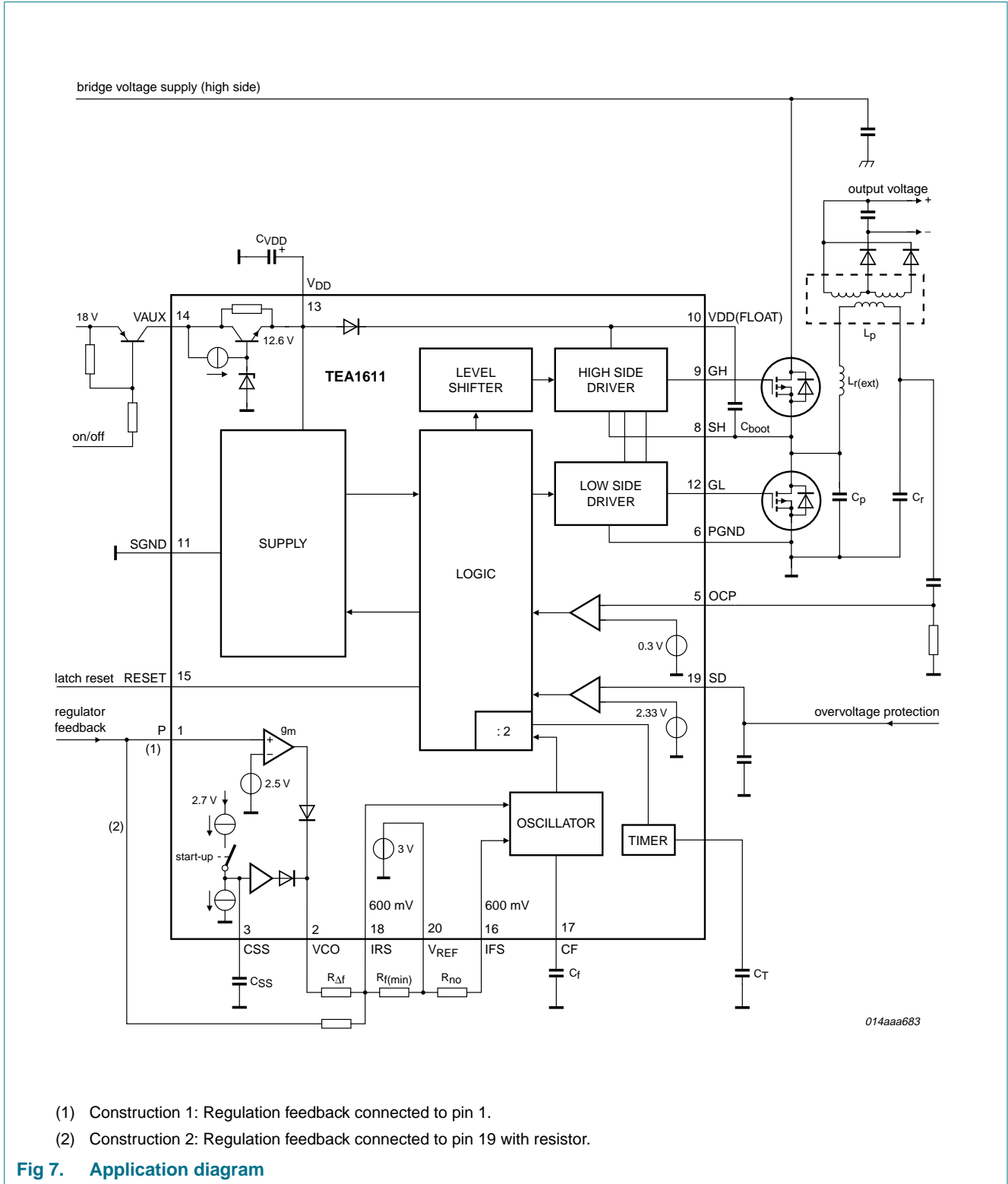
- [1] The supply current  $I_{DD}$  increases with an increasing bridge frequency to drive the capacitive load of two MOSFETs. Typical MOSFETs for the TEA1611T application are 8N50 (NXP type PHX80N50E,  $Q_{G(tot)} = 55\text{ nC typ.}$ ) and these will increase the supply current at 150 kHz according to the following formula:

$$\Delta I_{DD} = 2 \times Q_{G(tot)} \times f_{bridge} = 2 \times 55\text{ nC} \times 150\text{ kHz} = 16.5\text{ mA}$$

low side on; high side off;  $C_f = 100\text{ pF}$ ;  $I_{IFS} = 0.5\text{ mA}$ ;  $I_{IRS} = 50\text{ }\mu\text{A}$ ; low side off; high side off;  $V_{DD} = 9\text{ V}$

- [2] The frequency of the oscillator depends on the value of capacitor  $C_f$ , the peak-to-peak voltage swing  $V_{CF}$  and the charge/discharge currents  $I_{CF(ch)}$  and  $I_{CF(dis)}$ .

11. Application information



12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1

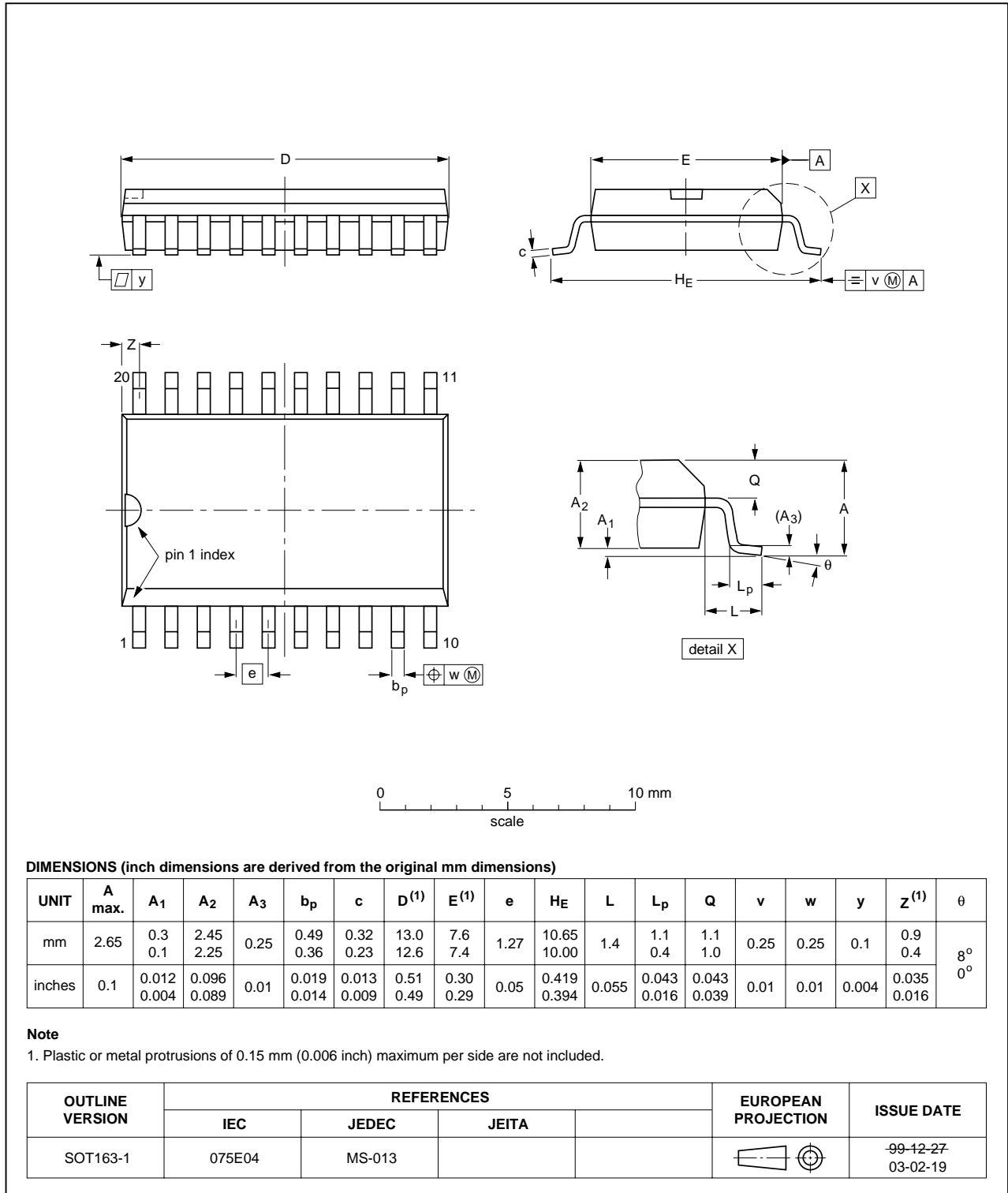


Fig 8. Package outline SOT163-1 (SO20)

## 13. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
TEA1611T_1	20090907	Product data sheet	-	-



## 14. Legal information

### 14.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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